

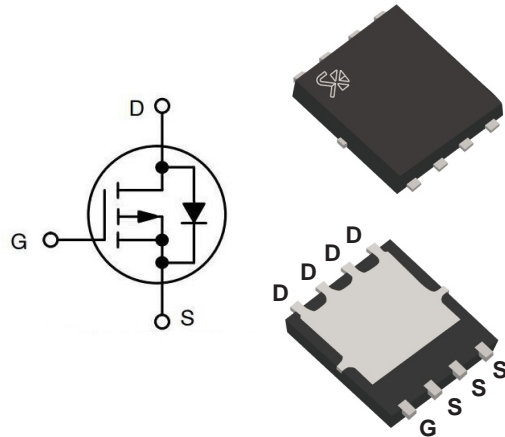
30V P-Channel MOSFET

Feature

- 30V P-Channel MOSFET High Dense Design.
- Ultra low On-Resistance.
- Reliable and Rugged.

Applications

- Power Management in Notebook Computer, and Portable Equipment and Battery Systems.



PDFN5060

Electrical Characteristics

Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-30V	V
Gate-Source Voltage	V _{GSS}	±20V	V
Drain Current-Continuous @ T _c =25°C	I _D	-50	A
Drain Current-Pulsed	I _{DM}	-200	A
Operating Junction Temperature Range	T _J	-55 to 150°C	°C

Electrical Characteristics(T_c=25°C unless otherwise noted)

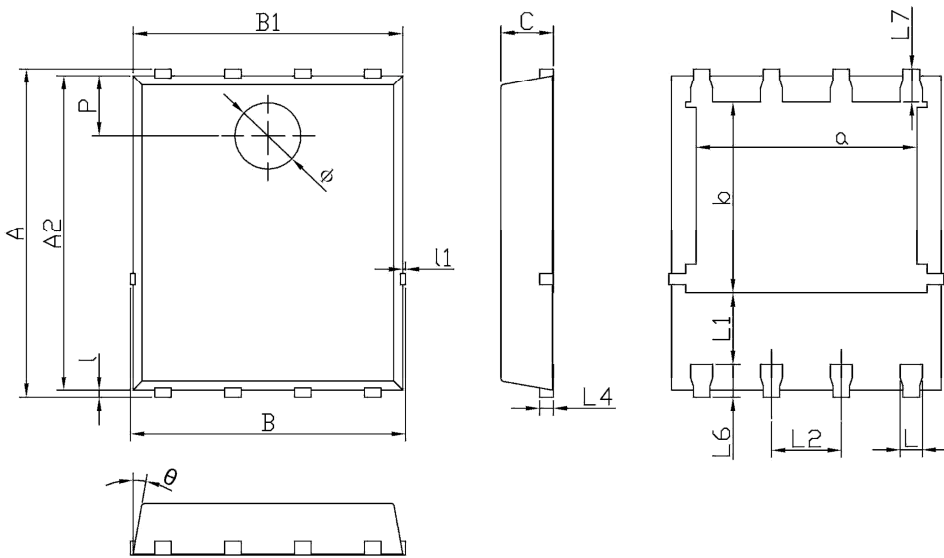
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTIC						
Drain-Source Breakdown Voltage	B _V DSS	V _G S=0V , I _D =-250uA	-30	-	-	V
Drain-Source Leakage Current	I _{DSS}	V _D S=-30V, V _G S=0V, T _J =25°C	-	-	-1	uA
Drain-Source Leakage Current	I _{DSS}	V _D S=-24V, V _G S=0V, T _J =125°C	-	-	-10	uA
Gate-Source Leakage Current	I _{GSS}	V _G S=±20V , V _D S=0V	-	-	±100	nA
ON CHARACTERISTIC						
Gate Threshold Voltage	V _G S(TH)	V _G S=V _D S, I _D =-250uA	-1.2	-1.6	-2.5	V
Static Drain-Source On-Resistance	R _D S(ON)	V _G S=-10V , I _D =-10A	-	7.1	8.5	mΩ
		V _G S=-4.5V , I _D =-8A	-	11.5	14	
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	V _D S=-15V, V _G S=0V, f=1MHz	-	3300	-	pF
Output Capacitance	C _{oss}		-	410	-	
Reverse Transfer Capacitance	C _{rss}		-	280	-	

NOTE:

1. The data tested by pulsed, pulse with ≤ 300us, duty cycle ≤ 2%.
2. R_DS(on) calculated by - package type.

PDFN5060

Unit:mm



Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	5.90	6.00	6.10
a	3.91	4.01	4.11
A2	5.70	5.75	5.80
B	4.90	5.00	5.10
b	3.37	3.47	3.57
B1	4.80	4.90	5.00
C	0.90	0.95	1.00
L	0.35	0.40	0.45
l	0.06	0.13	0.20
L1	1.10	-	-
l1	-	-	0.10
L2	1.17	1.27	1.37
L4	0.21	0.26	0.34
L6	0.51	0.61	0.71
L7	0.51	0.61	0.71
P	1.00	1.10	1.20
θ	8°	10°	12°
ϕ	1.10	1.20	1.30

单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)